# PMV170UN

# 20 V, single N-channel Trench MOSFET

**3 August 2012** 

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology

#### 1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	-	20	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	1.5	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 1 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	140	165	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





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### 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u> </u>	D 
2	S	source		
3	D	drain	1	G 13 7 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
				017aaa253

# 3. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PMV170UN	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				

## 4. Marking

Table 4. Marking codes

Table 11 manning course	
Type number	Marking code
	ឲ្យ
PMV170UN	EG%

<sup>[1] % =</sup> placeholder for manufacturing site code

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	20	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	1.5	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	1	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	0.9	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	4	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	325	mW
			[1]	-	455	mW
		T <sub>sp</sub> = 25 °C		-	1140	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain diode						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.7	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

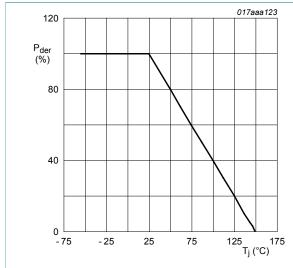


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

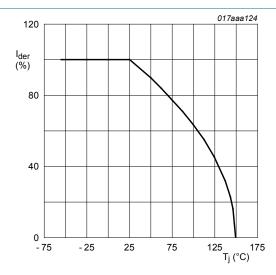


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{\textit{der}} = \frac{I_{\textit{D}}}{I_{\textit{D(25°C)}}} \times 100~\%$$

#### 20 V, single N-channel Trench MOSFET

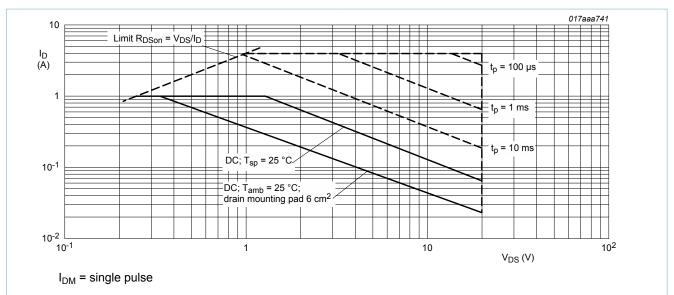


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient			[1]	-	333	385	K/W
			[2]	-	240	275	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	203	235	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	85	100	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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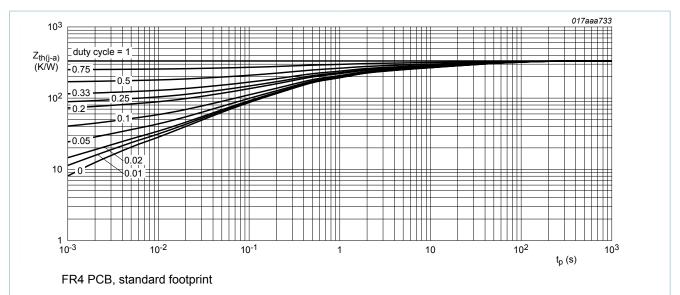


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

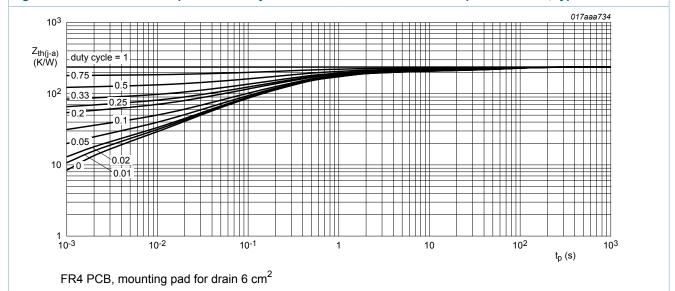


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = 250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	0.4	0.7	1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>amb</sub> = 150 °C	-	-	20	μA
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	140	165	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 1 A; T <sub>j</sub> = 150 °C	-	208	248	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	175	220	mΩ
		$V_{GS}$ = 1.8 V; $I_{D}$ = 0.25 A; $T_{j}$ = 25 °C	-	237	337	mΩ
9fs	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ A}; T_j = 25 \text{ °C}$	-	3.4	-	S
Dynamic cl	haracteristics		,			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ A}; V_{GS} = 4.5 \text{ V};$ $T_j = 25 \text{ °C}$	-	1.1	1.65	nC
$Q_{GS}$	gate-source charge		-	0.15	-	nC
$Q_{GD}$	gate-drain charge		-	0.3	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 10 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	83	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	37	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	26	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 1 A; V <sub>GS</sub> = 4.5 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	12	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	16	-	ns
t <sub>f</sub>	fall time		-	8	-	ns
Source-dra	in diode		l	1		
V <sub>SD</sub>	source-drain voltage	$I_S = 0.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.8	1.2	V
		,				

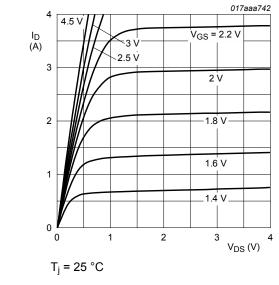


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

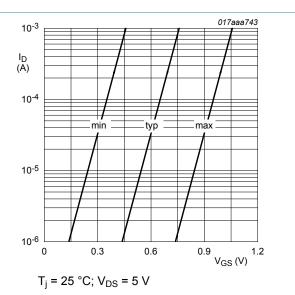


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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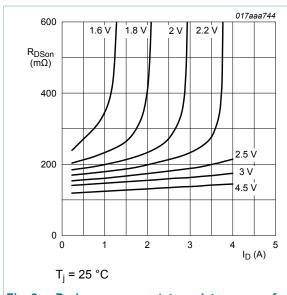


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

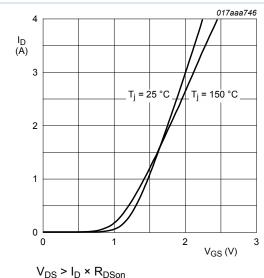


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

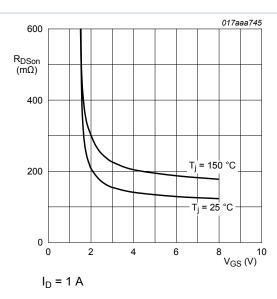


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

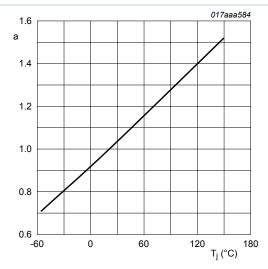


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

#### 20 V, single N-channel Trench MOSFET

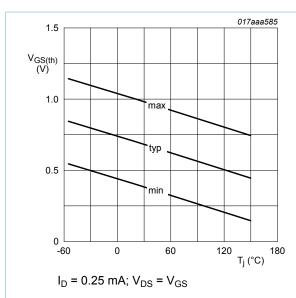


Fig. 12. Gate-source threshold voltage as a function of junction temperature

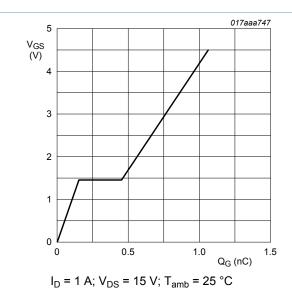


Fig. 14. Gate-source voltage as a function of gate charge; typical values

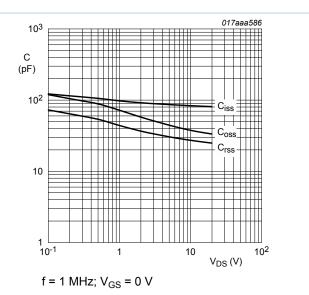


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

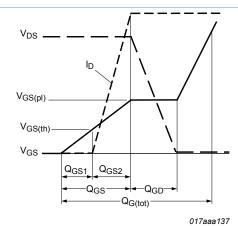
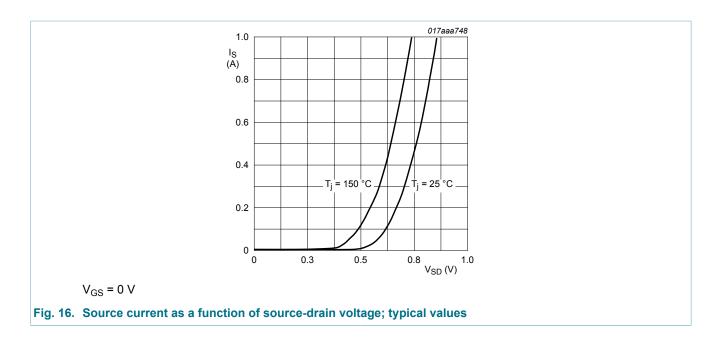
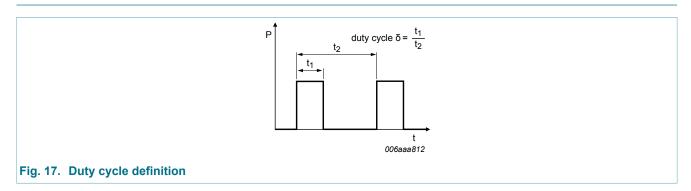


Fig. 15. Gate charge waveform definitions

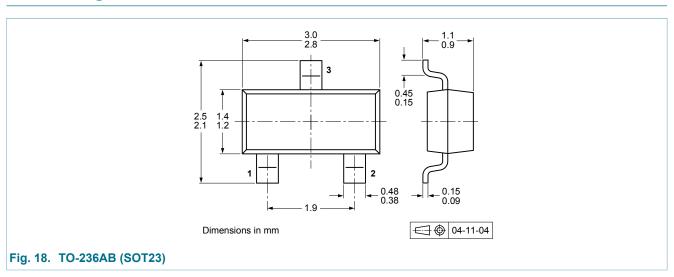
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### 8. Test information



# 9. Package outline

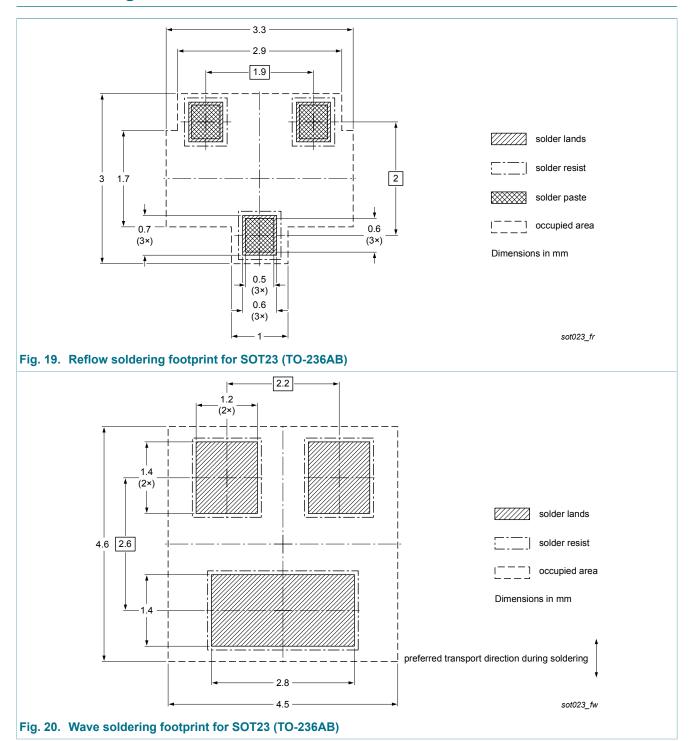


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### 10. Soldering



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# 11. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV170UN v.1	20120803	Product data sheet	-	-

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#### 20 V, single N-channel Trench MOSFET

### 12. Legal information

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